## Product Summary

| $BV_{DSS}$ | $R_{DS(ON)}$ max | $I_D$ max |
|---|---|---|
| 40V | 42mΩ @ $V_{GS}$ = 10V | 4.6A |
| | 52mΩ @ $V_{GS}$ = 4.5V | 4.1A |

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Description and Applications

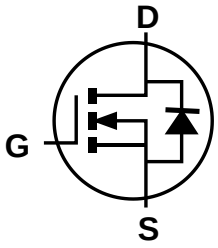
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

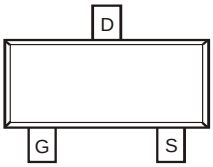
## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

Top View




Internal Schematic



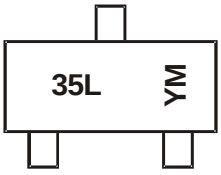

Top View

## Ordering Information (Note 5)

| Part Number | Case | Packaging |
|---|---|---|
| DMN4035LQ-7 | SOT23 | 3000/Tape & Reel |
| DMN4035LQ-13 | SOT23 | 10000/Tape & Reel |

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information




35L = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

| Year | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 |
|---|---|---|---|---|---|---|---|---|---|
| Code | G | H | I | J | K | L | M | N | O |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |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## Maximum Ratings (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DSS}$ | 40 | V |
| Gate-Source Voltage | | | $V_{GSS}$ | ±20 | V |
| Continuous Drain Current (Note 7) $V_{GS}$ = 10V | Steady State | $T_A$ = +25°C<br>$T_A$ = +70°C | $I_D$ | 4.6<br>3.7 | A |
| Maximum Body Diode Forward Current (Note 7) | | | $I_S$ | 1.5 | A |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | | | $I_{DM}$ | 25 | A |
| Pulsed Source Current (10µs Pulse, Duty Cycle = 1%) | | | $I_{SM}$ | 25 | A |

## Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|---|---|---|---|---|
| Power Dissipation (Note 6) | | $P_D$ | 0.72 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{\theta JA}$ | 171 | °C/W |
| Power Dissipation (Note 7) | | $P_D$ | 1.4 | W |
| Thermal Resistance, Junction to Ambient (Note 7) | Steady State | $R_{\theta JA}$ | 93 | °C/W |
| Operating and Storage Temperature Range | | $T_J$, $T_{STG}$ | -55 to +150 | °C |

## Electrical Characteristics (@$T_A$ = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS (Note 8)** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | 40 | — | — | V | $V_{GS}$ = 0V, $I_D$ = 250µA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | — | — | 1 | µA | $V_{DS}$ = 40V, $V_{GS}$ = 0V |
| Gate-Source Leakage | $I_{GSS}$ | — | — | ±100 | nA | $V_{GS}$ = ±20V, $V_{DS}$ = 0V |
| **ON CHARACTERISTICS (Note 8)** | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 1 | — | 3 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250µA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 30 | 42 | mΩ | $V_{GS}$ = 10V, $I_D$ = 4.3A |
| | | — | 40 | 52 | | $V_{GS}$ = 4.5V, $I_D$ = 3.9A |
| Diode Forward Voltage | $V_{SD}$ | — | 0.7 | 1.1 | V | $V_{GS}$ = 0V, $I_S$ = 1.25A |
| **DYNAMIC CHARACTERISTICS (Note 9)** | | | | | | |
| Input Capacitance | $C_{iss}$ | — | 574 | — | pF | $V_{DS}$ = 20V, $V_{GS}$ = 0V, f = 1MHz |
| Output Capacitance | $C_{oss}$ | — | 87.8 | — | | |
| Reverse Transfer Capacitance | $C_{rss}$ | — | 38.7 | — | | |
| Gate Resistance | $R_g$ | — | 1.6 | — | Ω | $V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz |
| Total Gate Charge ($V_{GS}$ = 4.5V) | $Q_g$ | — | 5.9 | — | nC | $V_{DS}$ = 20V, $I_D$ = 3.9A |
| Total Gate Charge ($V_{GS}$ = 10V) | $Q_g$ | — | 12.5 | — | | |
| Gate-Source Charge | $Q_{gs}$ | — | 1.7 | — | | |
| Gate-Drain Charge | $Q_{gd}$ | — | 2.2 | — | | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 3.1 | — | ns | $V_{DD}$ = 20V, $V_{GS}$ = 10V, $R_L$ = 20Ω, $R_G$ = 6Ω |
| Turn-On Rise Time | $t_R$ | — | 2.6 | — | | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 15 | — | | |
| Turn-Off Fall Time | $t_F$ | — | 5.5 | — | | |
| Reverse Recovery Time | $t_{RR}$ | — | 6.5 | — | ns | $I_F$ = 3.9A, di/dt = 500A/µs |
| Reverse Recovery Charge | $Q_{RR}$ | — | 1.2 | — | nC | |

Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.


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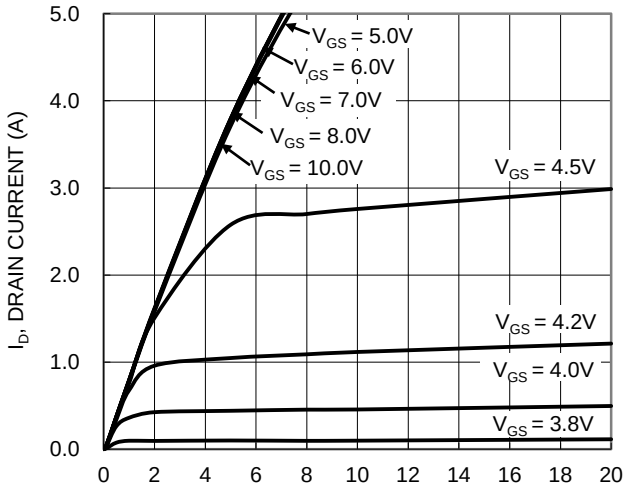


Figure 1. Typical Output Characteristic

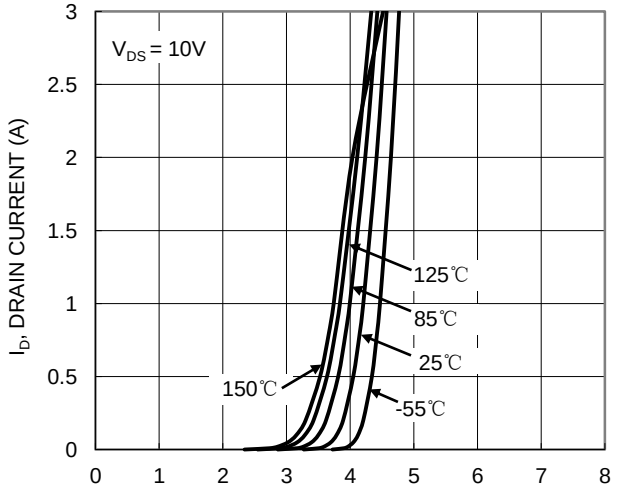


Figure 2. Typical Transfer Characteristic

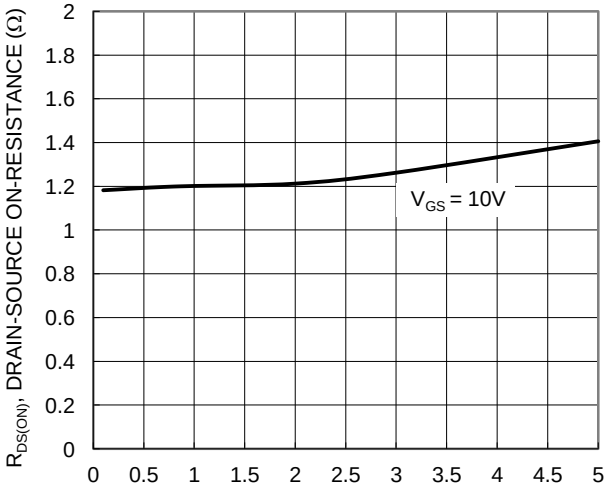


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

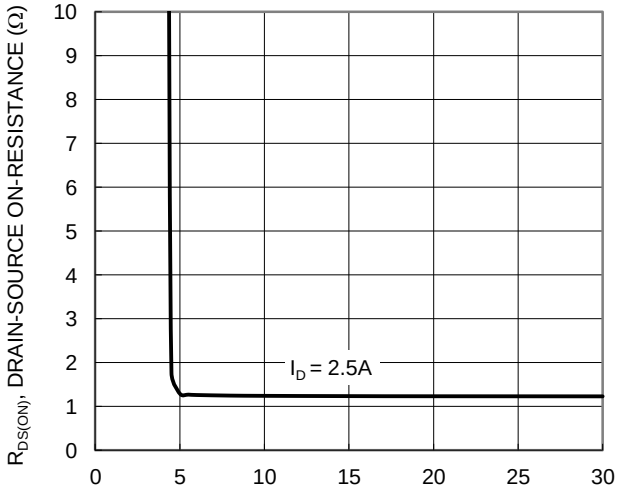


Figure 4. Typical Transfer Characteristic

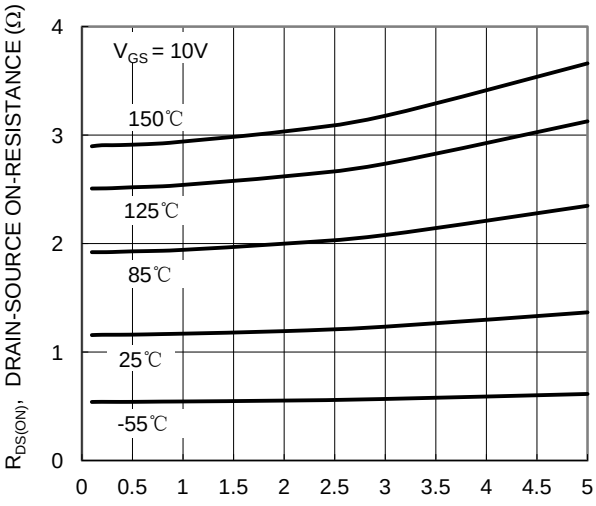


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

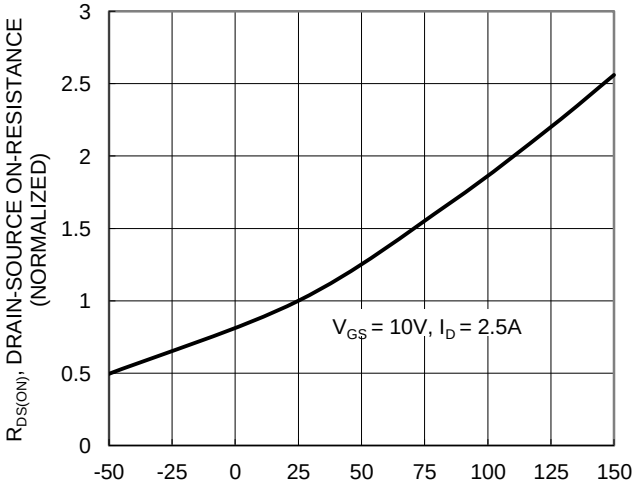


Figure 6. On-Resistance Variation with Temperature


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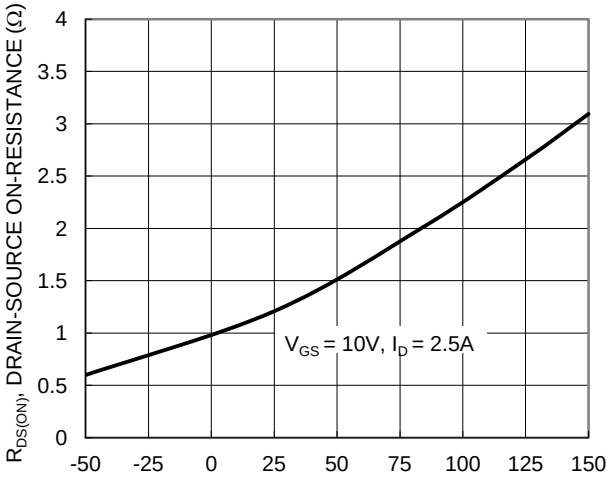


Figure 7. On-Resistance Variation with Temperature

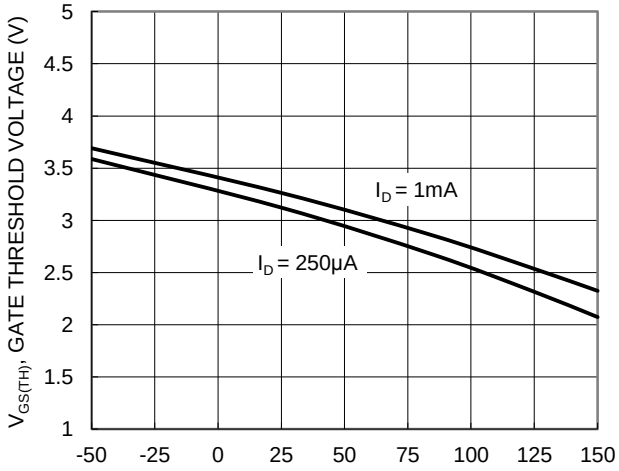


Figure 8. Gate Threshold Variation vs. Junction Temperature

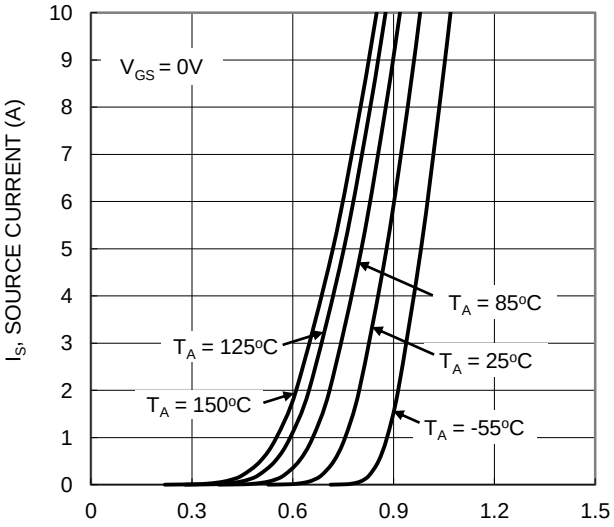


Figure 9. Diode Forward Voltage vs. Current

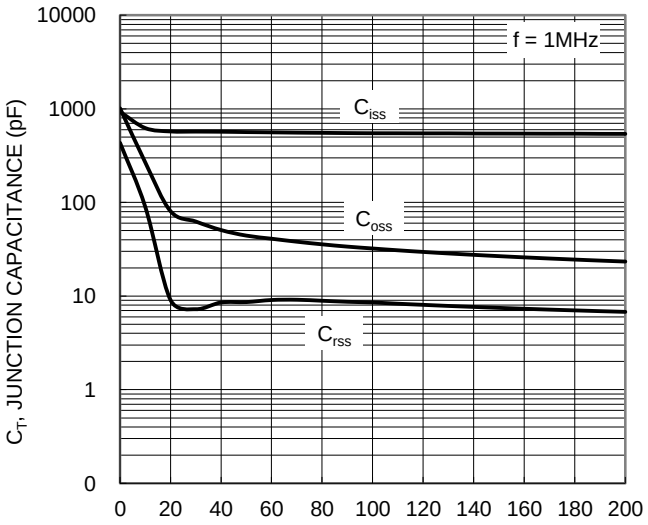


Figure 10. Typical Junction Capacitance

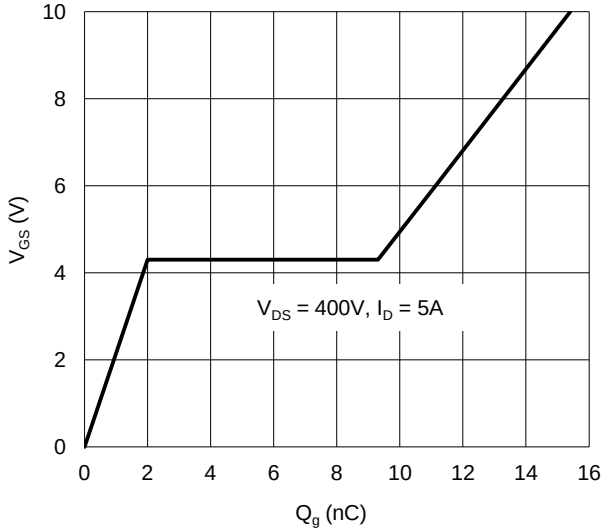


Figure 11. Gate Charge

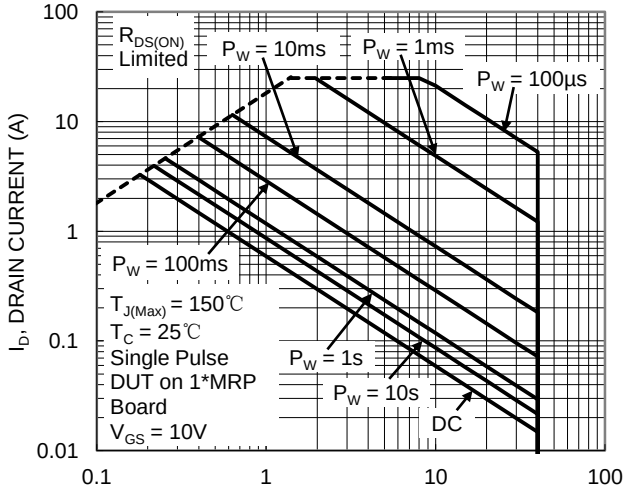


Figure 12. SOA, Safe Operation Area


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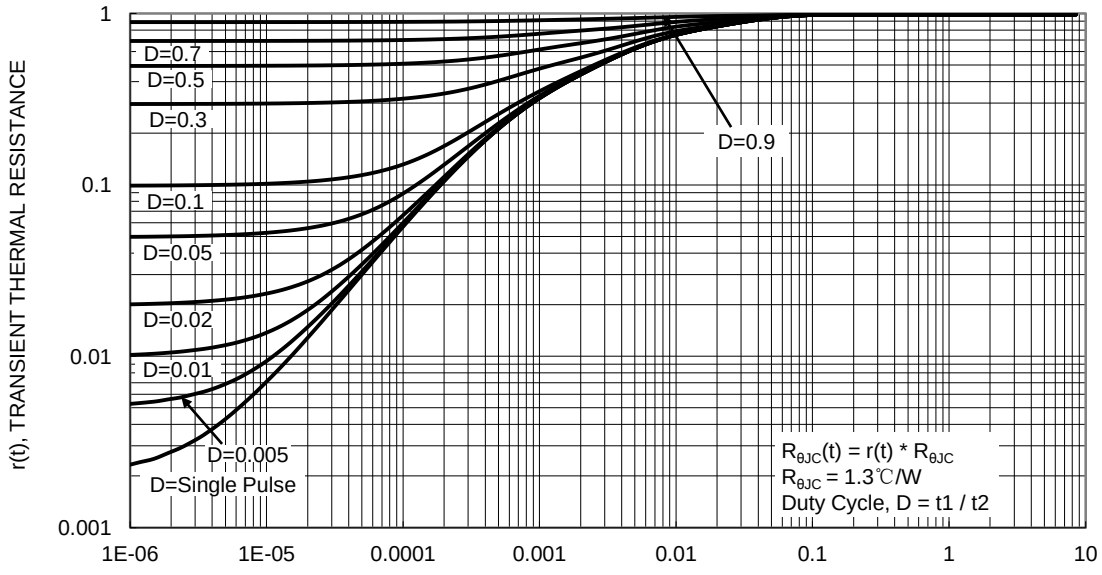


Figure 13. Transient Thermal Resistance


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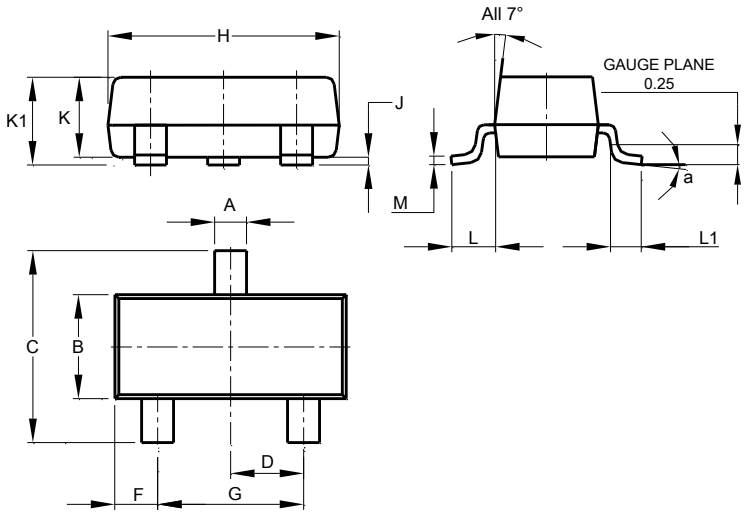
## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

**SOT23**

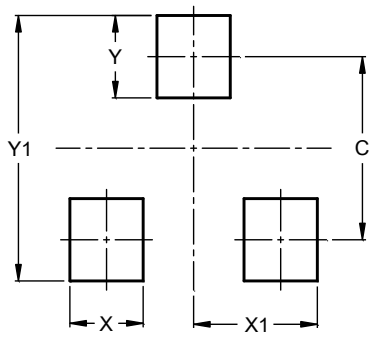



| SOT23 | | | |
|---|---|---|---|
| **Dim** | **Min** | **Max** | **Typ** |
| **A** | 0.37 | 0.51 | 0.40 |
| **B** | 1.20 | 1.40 | 1.30 |
| **C** | 2.30 | 2.50 | 2.40 |
| **D** | 0.89 | 1.03 | 0.915 |
| **F** | 0.45 | 0.60 | 0.535 |
| **G** | 1.78 | 2.05 | 1.83 |
| **H** | 2.80 | 3.00 | 2.90 |
| **J** | 0.013 | 0.10 | 0.05 |
| **K** | 0.890 | 1.00 | 0.975 |
| **K1** | 0.903 | 1.10 | 1.025 |
| **L** | 0.45 | 0.61 | 0.55 |
| **L1** | 0.25 | 0.55 | 0.40 |
| **M** | 0.085 | 0.150 | 0.110 |
| **a** | 0° | 8° | -- |
| **All Dimensions in mm** | | | |

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

**SOT23**




| Dimensions | Value (in mm) |
|---|---|
| **C** | 2.0 |
| **X** | 0.8 |
| **X1** | 1.35 |
| **Y** | 0.9 |
| **Y1** | 2.9 |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